University of California, Berkeley EECS 240 Spring 2006 Prof. A. Niknejad

## Problem Set 4 Due Thursday February 23, 2006

1. For the current mirror below, calculate the maximum value of R that results in less than one percent mismatch, i.e.  $I/I_{ref} < 0.01$ . Ignore all other sources of current mismatch. Both transistors are the same size. (a) Bias both transistors at  $V^* = 500$ mV. (b) Same, but bias the transistors in weak inversion (n = 1.5). (c) Calculate the total output noise of the current source. Draw up instructions for the layout draftsman to meet the resistance constraints.



- 2. Find the minimum width and length for two 1k poly resistors with 0.2% matching with a yield of 89%. Poly sheet resistance:  $100\Omega/square$ , standard deviation of the width: W = 20nm.
- 3. Find an expression for the transconductance of M1 as a function of R and m. Assume that the mirror has an exact 1:1 ratio, and neglect the body effect. Add a startup circuit.



4. Calculate the minimum value of ISS to meet specifications for  $f_{-3 \text{ dB}}$ ,  $\overline{v_{oT}^2}$ ,  $V_1^*$  and  $V_2^*$ . Definitions:  $f_{-3 \text{ dB}}$  is the frequency at which the gain drops by 3dB from it's

value at DC;  $\overline{v_{oT}^2}$  is the total noise integrated over all frequencies at the output of the amplifier;  $V_1^*$  and  $V_2^*$  are the bias points of M1, M1' and M2, M2', respectively. Assume all devices operate in saturation and ignore finite output resistance.

